

40V P-Channel Enhancement Mode MOSFET

Description

The PECN14P04SR uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in load switch and battery protection applications.

General Features

- ◆ $V_{DS} = -40V$, $I_D = -14A$
 $R_{DS(ON)}(Typ.) = 12m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)}(Typ.) = 8.5m\Omega$ @ $V_{GS} = -10V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

- ◆ Adapter switch
- ◆ Load switch
- ◆ Battery switch
- ◆ Motor drive control

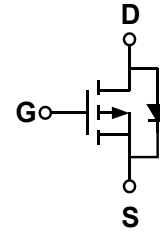
Package

- ◆ SOP-8

100% UIS TESTED!

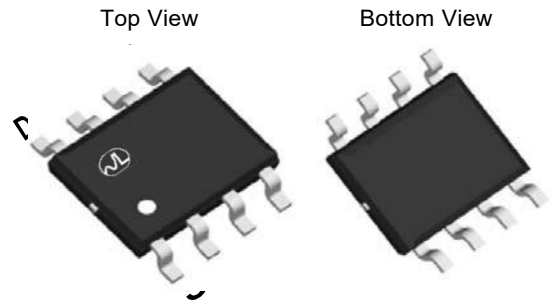
100% ΔV_{ds} TESTED!

Schematic diagram



Marking and pin assignment

SOP-8



XXXX—Wafer Lot No.

YYYY—Quality Code



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PECN14P04S R-G	-55°C to +150°C	SOP-8	4000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	-14	A
	$T_C = 70^\circ C$		-11 ^{b,c}	
	$T_A = 25^\circ C$		-9.9 ^{b,c}	
	$T_A = 70^\circ C$		-7.9	
Pulsed Drain Current		I_{DP}	-80 ^a	
Continuous source-drain diode current		I_S	-4.5	

	$T_A=70^{\circ}\text{C}$		-2.2 ^{b,c}	
Single pulse avalanche current	$L=0.1\text{mH}$	I_{AS}	-20	A
Single pulse avalanche energy		E_{AS}	20	mJ
Maximum power dissipation	$T_C=25^{\circ}\text{C}$	P_D	5	W
	$T_C=70^{\circ}\text{C}$		3,2	
	$T_A=25^{\circ}\text{C}$		2.5 ^{b,c}	
	$T_A=70^{\circ}\text{C}$		1.6 ^{b,c}	
Operating junction and storage temperature range		T_J, T_{STG}	-55—150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter		Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient ^{b,d}	$\leq 10\text{s}$	$R_{\theta JA}$	40	50	$^{\circ}\text{C/W}$
Maximum Junction-to-Ambient ^a	Steady-State		59	75	
Maximum Junction-to-Lead ^b	Steady-State	$R_{\theta JC}$	21	25	

a. Package limited b. Surface mounted on 1" x 1" FR4 board

c. $t = 10\text{ s}$ d. Maximum under steady state conditions is 85°C/W

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-40	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	μA
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
ON Characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.4	-2.0	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	8.5	14	mΩ
		V _{GS} =-4.5V, I _D =-10A		12	18	
Forward transconductance	g _{fs}	V _{DS} =-10V, I _D =-10A	-	45	-	S
Dynamic Characteristics						
Input capacitance	C _{ISS}	V _{DS} =-20V ,V _{GS} =0V f=1.0MHz	-	3670	-	pF
Output capacitance	C _{OSS}		-	299	-	
Reverse transfer capacitance	C _{RSS}		-	237	-	
Switching Characteristics						
Turn-on delay time	t _{D(ON)}	V _{DS} =-20V R _L =2Ω V _{GS} =-10V R _{GEN} =1Ω	-	12	-	ns
Rise time	t _r		-	6	-	
Turn-off delay time	t _{D(OFF)}		-	44	-	
Fall time	t _f		-	6	-	
Total gate charge	Q _g	V _{DS} =-20V,I _D =-14A V _{GS} =-10V	-	66	-	nC
Gate-source charge	Q _{gs}		-	9.8	-	

Gate-drain charge	Qgd		-	10	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=-1.0A$	-	-0.8	-1.1	V

Typical Performance Characteristics

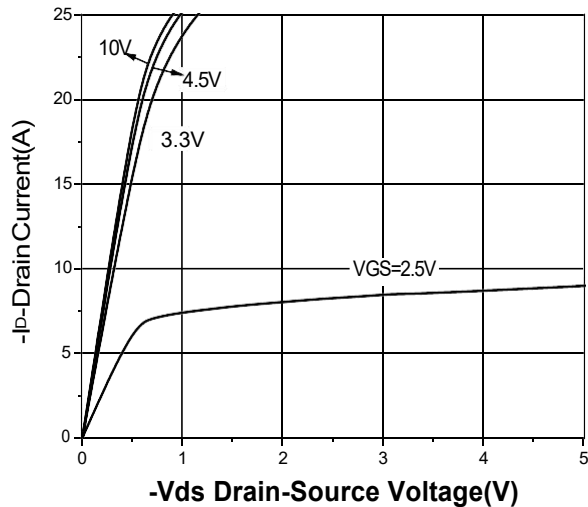


Fig1 Output Characteristics

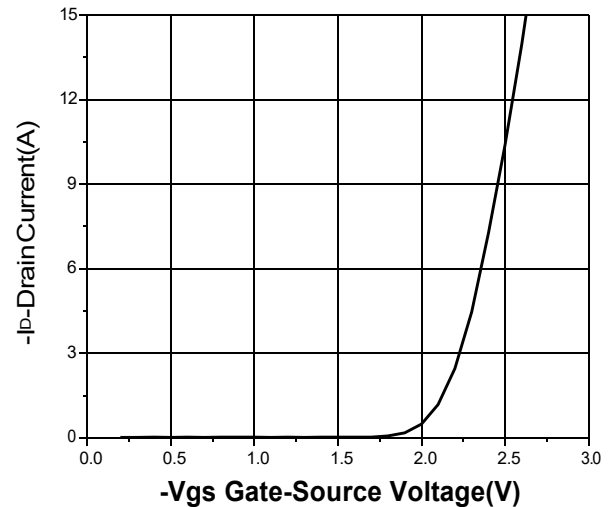


Fig2 Transfer Characteristics

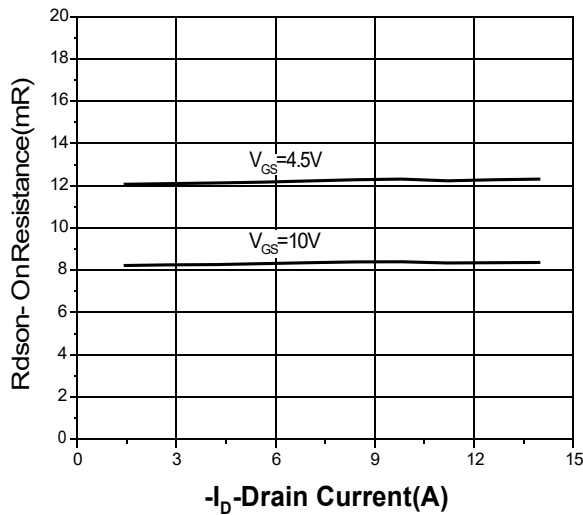


Fig3 Rdson-Drain current

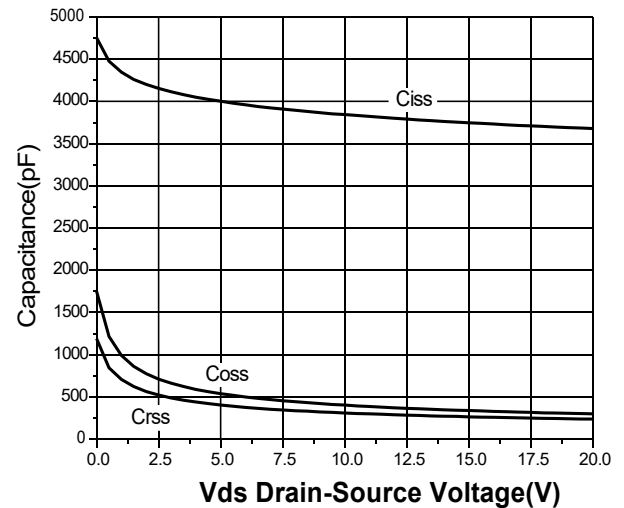


Fig4 Capacitance vs Vds

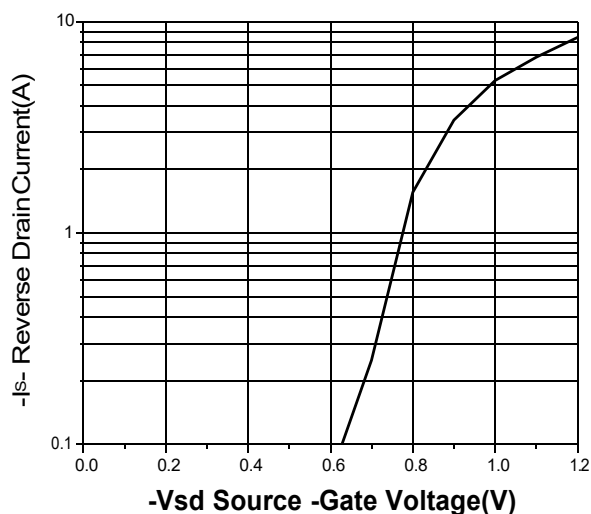


Fig5 Source-Drain Diode Forward

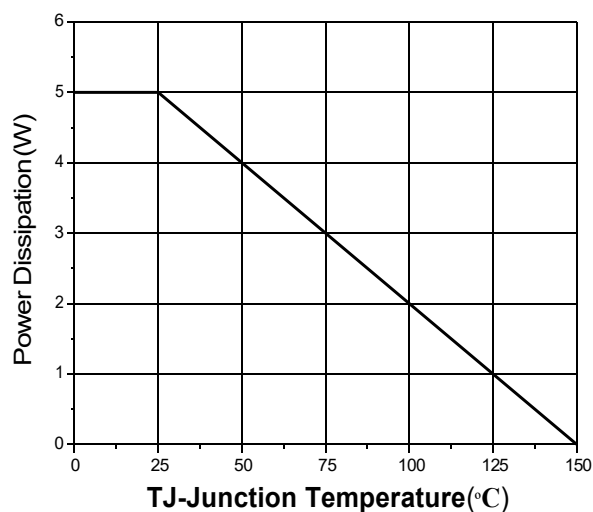


Fig6 Power De-rating

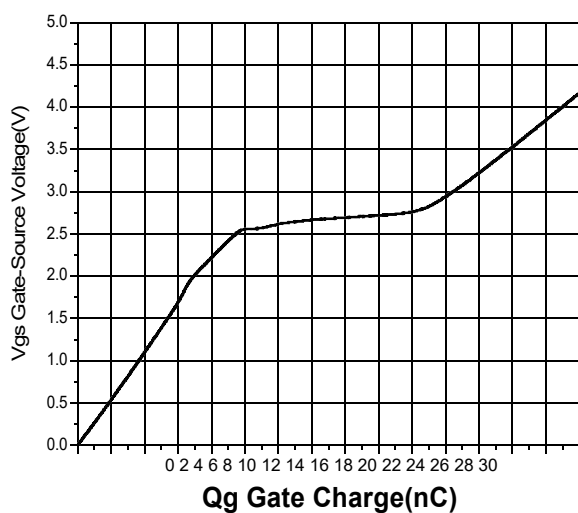


Fig7 Gate Charge

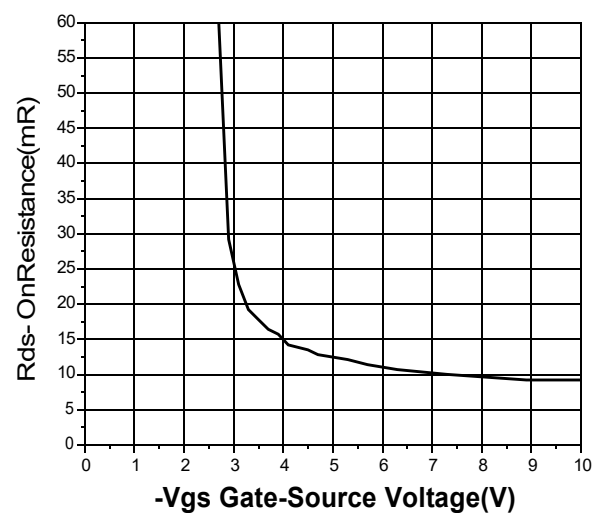
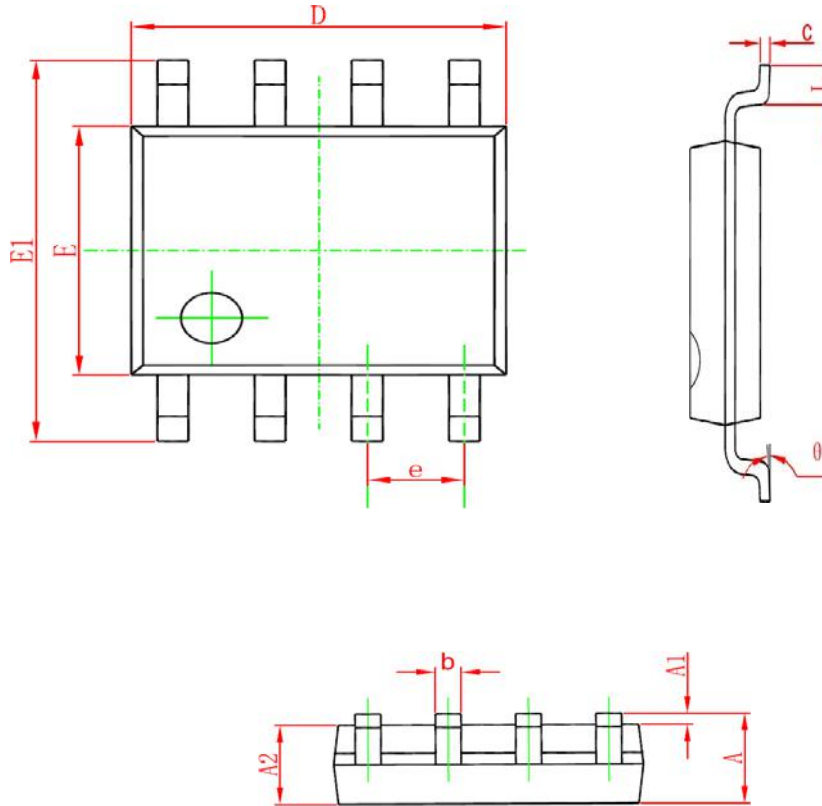


Fig8 Rdson-Gate Source voltage

Package Information

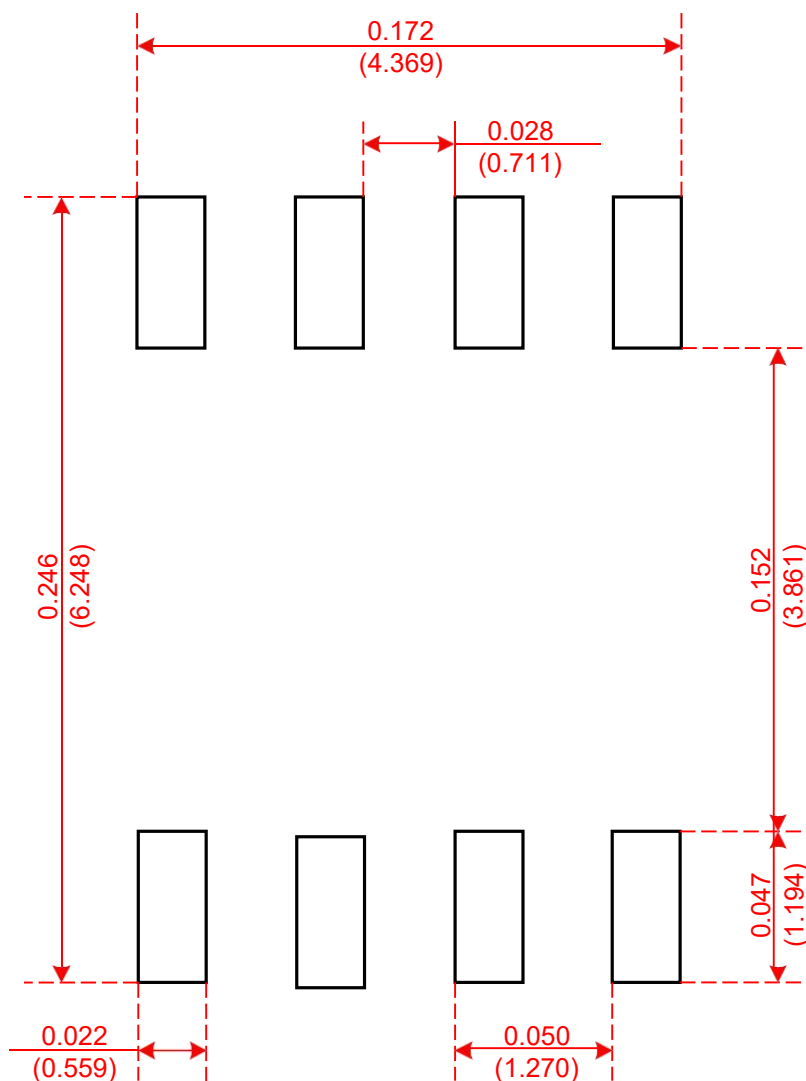
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Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Recommended Minimum Pads

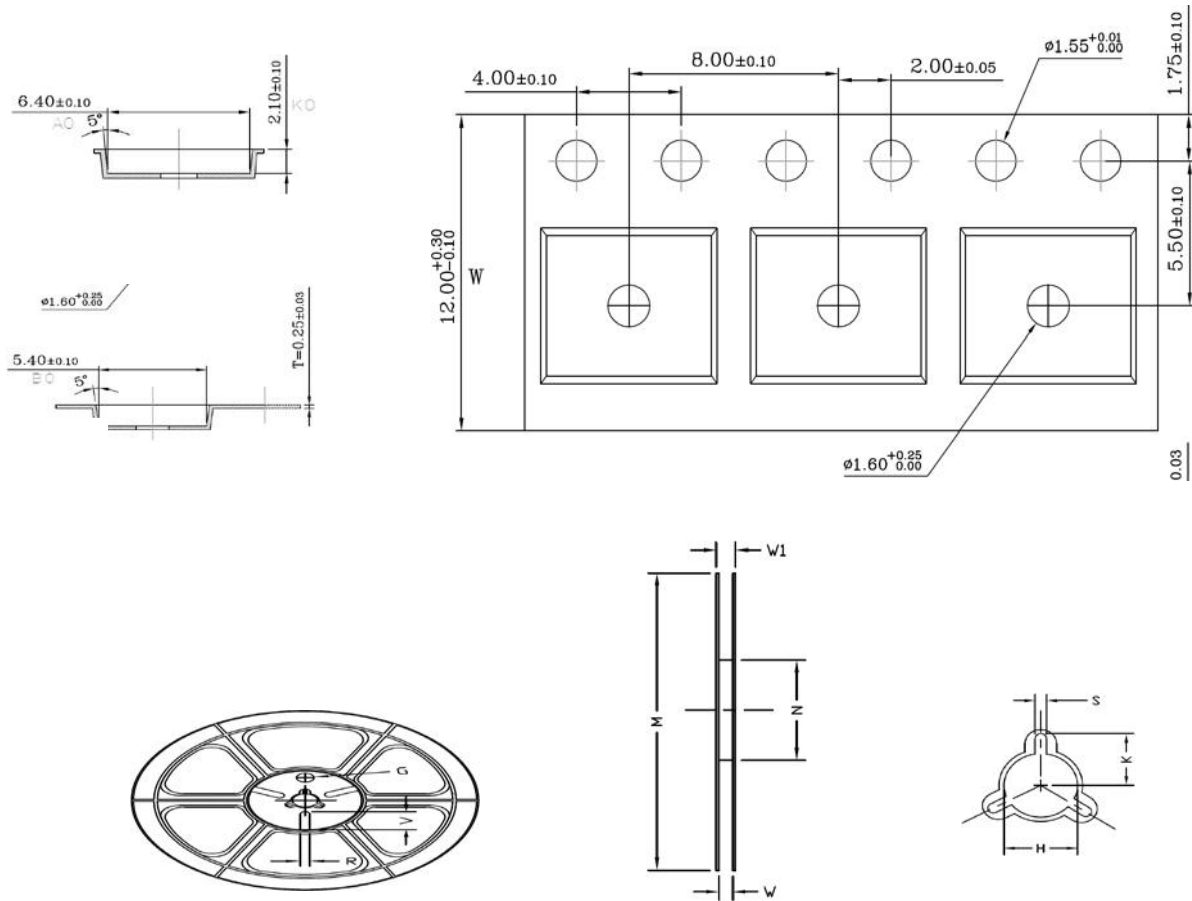
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Recommended Minimum Pads
Dimensions in Inches/(mm)

Tape and Reel

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Tape Size	Reel Size	M	N	W	W1	H	K	S	G	R	V
12mm	Φ330	Φ330.00 ±0.50	Φ97.00 ±0.30	13.00 ±0.30	17.40 ±1.00	Φ13.00 ±0.5	10.6	2.00 ±0.50	—	—	—

Unit Per Reel:
4000pcs

